Ordering number: EN4135

PNP/NPN Epitaxial Planar Silicon Transistor





50V/4A Switching Applications

Applications

· Power supplies, relay drivers, lamp drivers.

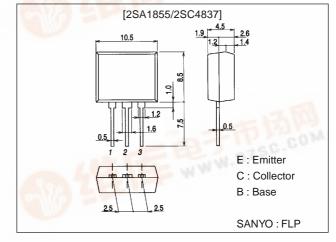
Features

- · Adoption of FBET and MBIT processes.
- · Large allowable collector dissipation.
- · Low saturation voltage.
- · Wide ASO and large current capacity.
- · Usage of radial taping to meet automatic mounting.

Package Dimensions

unit:mm

2084B



(): 2SA1855

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(-)60	V
Collector-to-Emitter Voltage	V _{CEO}		(-)50	V
Emitter-to-Base Voltage	V _{EBO}	148	(-)6	V
Collector Current	IC	Aure E	(-)4	Α
Colletor Current (Pulse)	ICP	- Lib (1977)	(-)6	Α
Collector Dissipation	PC	ALL LEE	1.5	W
Junction Temperature	Tj	ACT LEL	150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Dovomator	Symbol	Conditions		Ratings		
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} =(-)40V, I _E =0			(-)1	μΑ
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0			(-)1	μΑ
DC Current Gain	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)10mA	100*	-	400*	
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)3A	40		40.3	; D !"
Gain Bandwidth Product	f _T	V _{CE} =(-)10V, I _C =(-)50mA		150		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)10V, f=1MHz	A A	(39)25		pF

^{* :} The 2SA1855/2SC4837 are classified by 100mA $h_{\mbox{\scriptsize FE}}$ as follows :

100	R	200	140	S	280	200	Т	400

- Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.
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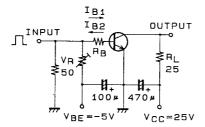
SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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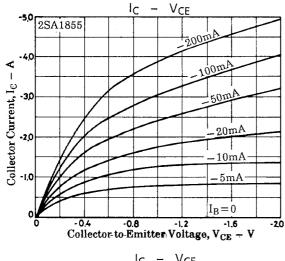
Parameter	Cumahad	Conditions		Unit		
Farameter	Symbol	Conditions		typ	max	Utill
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)2A, I _B =(-)100mA		(-350)	(-700)	mV
				190	500	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)2A, I _B =(-)100mA		(-)0.94	(-)1.2	V
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =-10μA, I _E =0	(–)60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =-1mA, R _{BE} =∞	(–)50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =-10μA, I _C =0	(–)6			V
Turn-ON Time	ton	See specified Test CIrcuit		70		ns
Storage Time	t _{stg}	See specified Test Clrcuit		(450)		ns
				650		ns
Fall Time	t _f	See specified Test Circuit		(30)35		ns

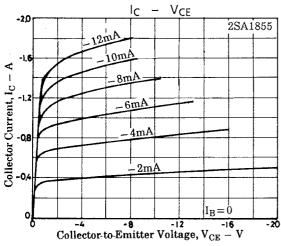
Switching Time Test Circui

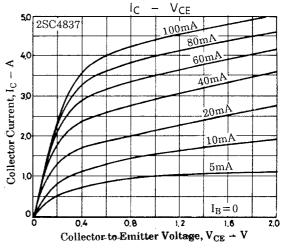
PW=20μs DC≦1%

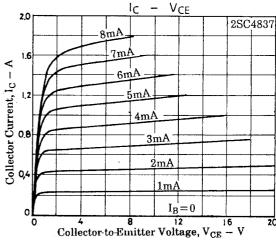


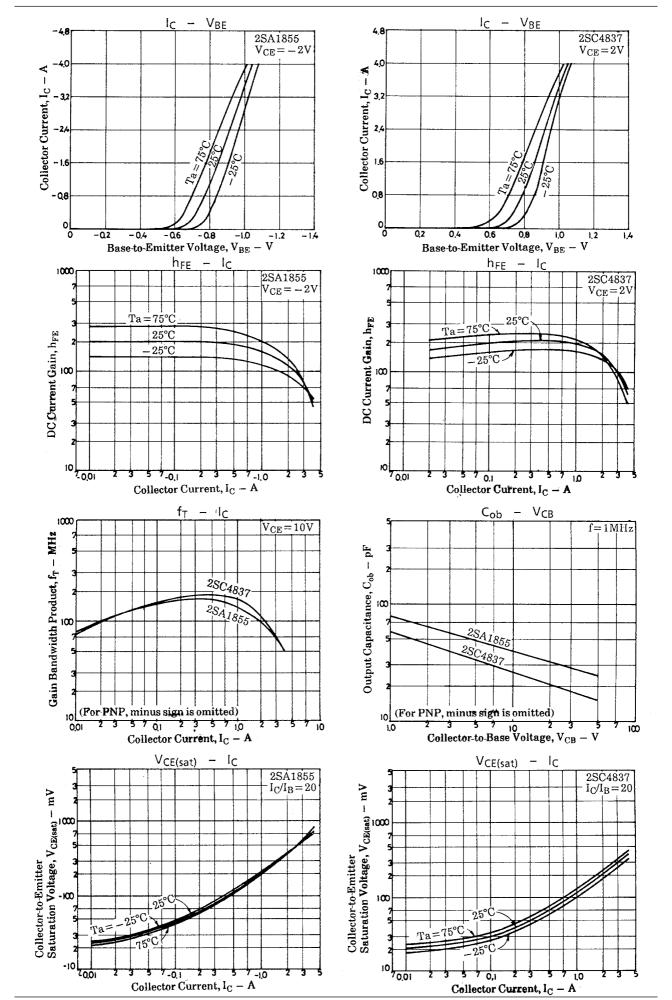
 $\begin{array}{l} I_C\!=\!10I_B1\!=\!-10I_B2\!=\!1A & \text{Access} \\ \text{Unit (resistance}:\Omega, capacitance}:\text{F)} \end{array}$



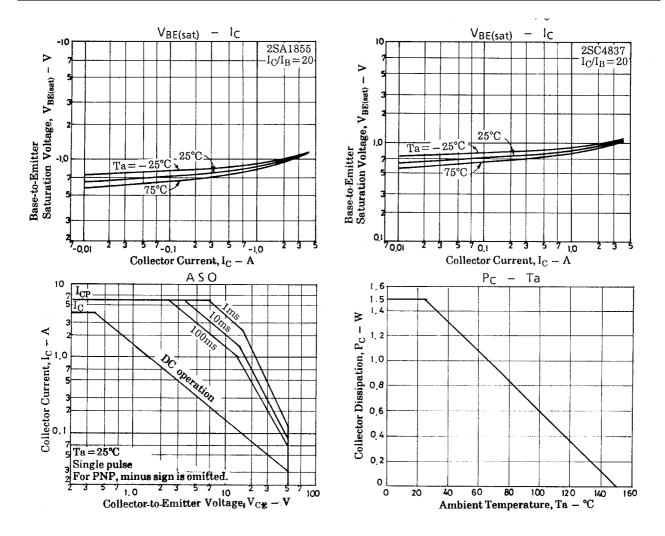








2SA1855/2SC4837



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